

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	51146	(mov\$3 or lower\$3) same (diffuser or baffle) same (air or bubble\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:47
L2	52607	(mov\$3 or lower\$3 or rais\$3) same (diffuser or baffle) same (air or bubble\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:50
L3	988	l2 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:47
L4	514	l3 and (surface with (air or bubble\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:52
L5	276	l4 and (electroplat\$10 or electrodeposit\$10 or electroly\$10 or electrochem\$10)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:53
L6	10789	(mov\$3 or lower\$3 or rais\$3) with (article or wafer or substrate or semiconductor or work\$2piece) with (diffuser or baffle or barrier)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:52
L7	6582	l6 and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:52

## EAST Search History

L8	0	l36and (surface with (air or bubble\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:52
L9	906	l6 and (surface with (air or bubble\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 15:52
L10	173	l9 and (electroplat\$10 or electrodeposit\$10 or electroly\$10 or electrochem\$10)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 16:53
L11	316	205/137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2007/04/23 16:53